SB039C025-0.5-W-Ag

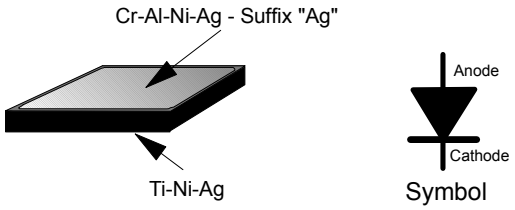
Schottky cr Barrier Diode Wafer

39 Mils, 25 Volt, 0.5 Amp, 0.34$V_{F.}$

Data Sheet

Features

Oxide Passivated Junction
Very Low Forward Voltage
125 ° C Junction Operating
Low Reverse Leakage
Supplied as Wafers
Chromium Barrier
>1000V ESD (MM)



Electrical Characteristics @ 25°C	Symbol	Unit	SB039C025-0.5-W-Ag (See ordering code below)
Maximum Repetitive Reverse Voltage (2)	V_{RRM}	Volt	25
Maximum Forward Voltage @ I_F = 0.5A (1)(2)	V_F	Volt	0.34
Typical Average Forward Rectified Current (2)	$I_{F(AV)}$	Amp	0.5
Reverse Leakage Current @ V_R = 25V (2)	$I_{R(1)}$	µA	500
Reverse Leakage Current @ V_R = 25V, 125°C (2)	$I_{R(2)}$	mA	15
ESD Machine Model (MM)	$V_{ESD(mm)}$	Volt	>1000
Junction Operating Temperature Range (2)	T_J	°C	-45 to +125
Storage Temperature Range (2)	T_{SG}	°C	-45 to +125

(1) Pulse Width tp = < 300µS, Duty Cycle <2%
(2) The characteristics above assume the die are assembled in industry standard packages using appropriate attach methods.

e.g. Ordering Code

SB065C040-3-W-Ag

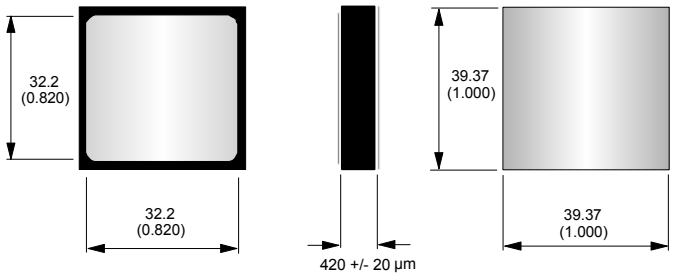
Schottky Barrier | 65 Mils | CR Barrier | 40Volt | 3 Amp | Wafer CR/Ti/Ni/Ag

Mechanical Dimensions

Wafer

- Wafer Diameter - 100 mm (4")
- Wafer Thickness 420 +/- 20
- Top (Anode) - CR/Ti/Ni/Ag (Suffix "Ag")
- Bottom (cathode) Ti/Ni/Ag
- Scribe line Width 80 µM

Die



Third Angle Protection

Dimensions in mils (mm)

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